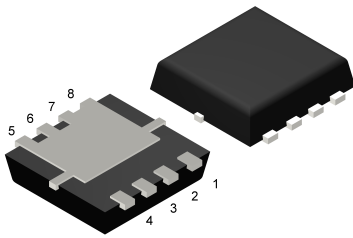
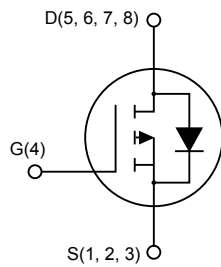


P-channel -30 V, 12 mΩ typ., -9 A STripFET™ H6 Power MOSFET in a PowerFLAT™ 3.3x3.3 package



PowerFLAT™ 3.3x3.3



AM01475v4

Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STL9P3LLH6	-30 V	15 mΩ	-9 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is a P-channel Power MOSFET developed using the STripFET™ H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low $R_{DS(on)}$ in all packages.

Product status

STL9P3LLH6

Product summary

Order code	STL9P3LLH6
Marking	9P3L
Package	PowerFLAT™ 3.3x3.3
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	-30	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	-9	A
I_D	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	-5.9	A
$I_{DM}^{(1)}$	Drain current (pulsed)	-36	A
P_{TOT}	Total dissipation at $T_{pcb}=25\text{ }^\circ\text{C}$	3	W
T_{stg}	Storage temperature range	- 55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	42	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu t < 10 s

2 Electrical characteristics

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Table 3. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = -1\text{ mA}$	-30			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = -30\text{ V}$			-1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = -30\text{ V}, T_C = 125\text{ }^\circ\text{C}$ ⁽¹⁾			-10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1			V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = -10\text{ V}, I_D = -4.5\text{ A}$		12	15	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -4.5\text{ A}$		18	22.5	m Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = -25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0\text{ V}$	-	2615	-	pF
C_{oss}	Output capacitance		-	340	-	pF
C_{riss}	Reverse transfer capacitance		-	235	-	pF
Q_g	Total gate charge	$V_{DD} = -15\text{ V}, I_D = -9\text{ A},$	-	24	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = -4.5\text{ to }0\text{ V}$ (see Figure 13. Gate charge test circuit)	-	9	-	nC
Q_{gd}	Gate-drain charge		-	8	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = -15\text{ V}, I_D = -4.5\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = -10\text{ V}$ (see Figure 12. Switching times test circuit for resistive load)	-	13.2	-	ns
t_r	Rise time		-	93	-	ns
$t_{d(off)}$	Turn-off delay time		-	50	-	ns
t_f	Fall time		-	18	-	ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = -9\text{ A}, V_{GS} = 0\text{ V}$	-		-1.1	V

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_{SD} = -9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	20		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = -24\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	16		nC
I_{RRM}	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	-1.6		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Note: Note: For the P-channel Power MOSFET, current and voltage polarities are reversed.

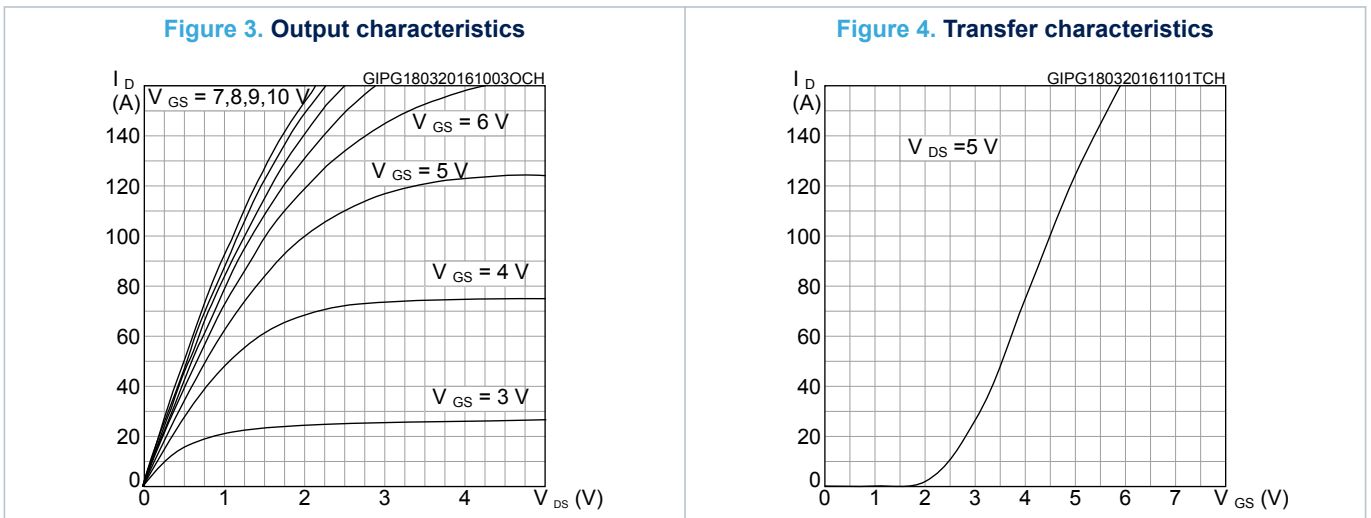
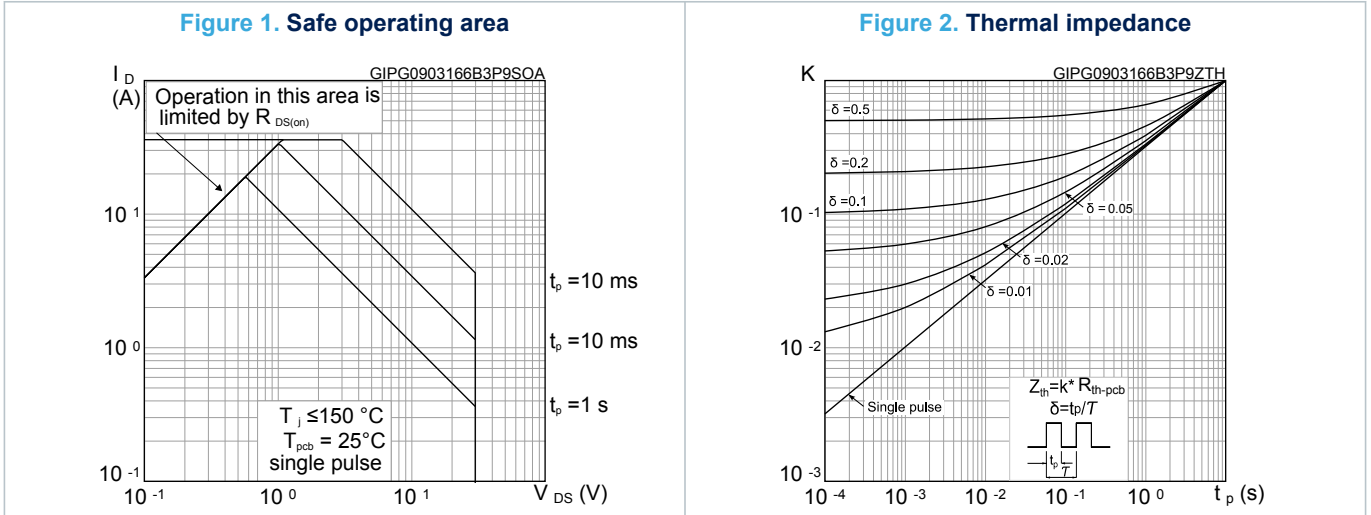


Figure 5. Gate charge vs gate-source voltage

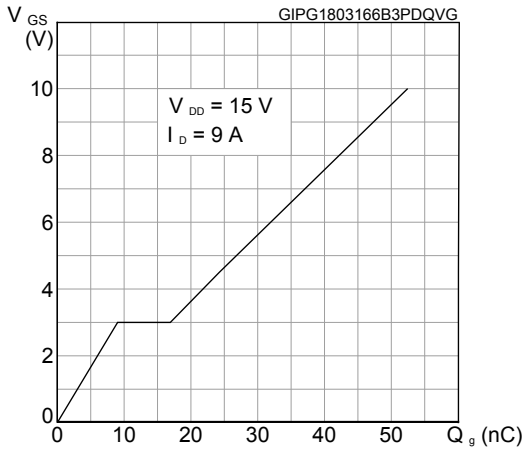


Figure 6. Static drain-source on-resistance

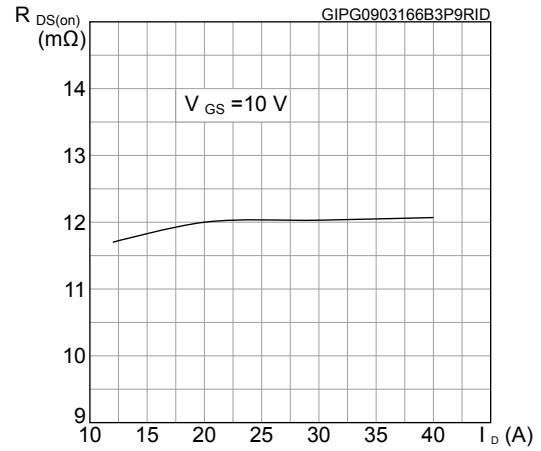


Figure 7. Capacitance variations

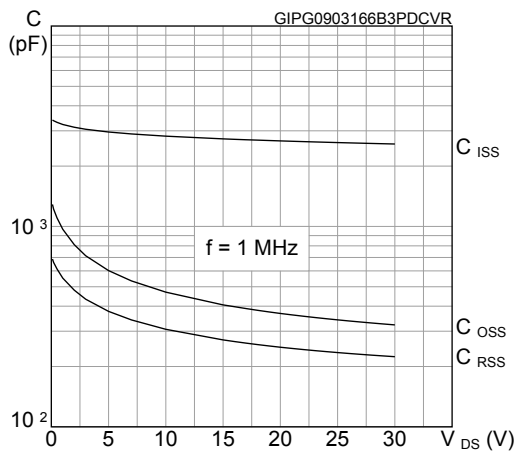


Figure 8. Normalized gate threshold voltage vs temperature

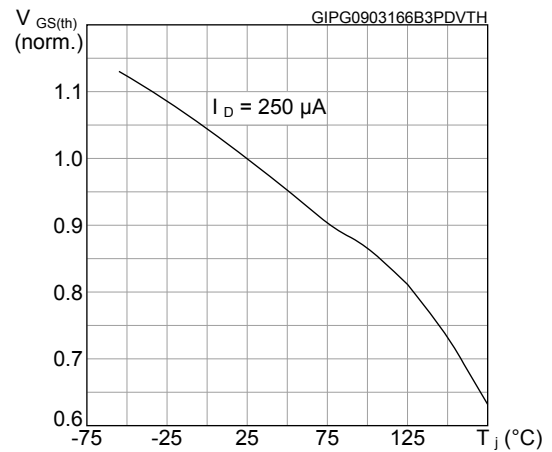


Figure 9. Normalized on-resistance vs temperature

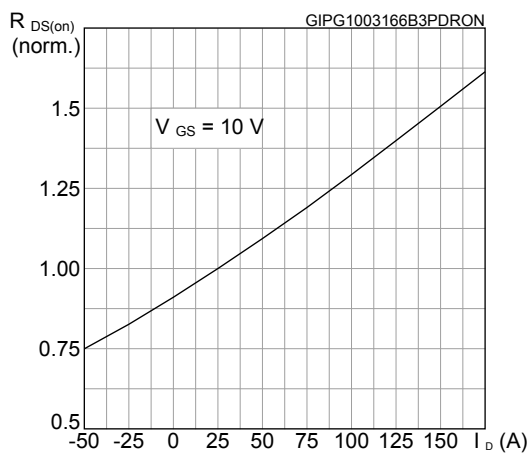


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

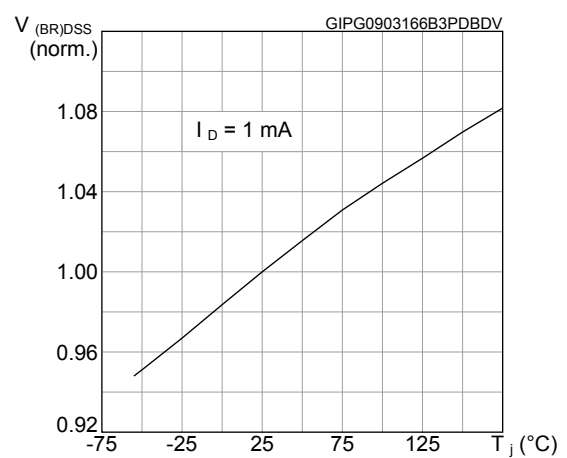
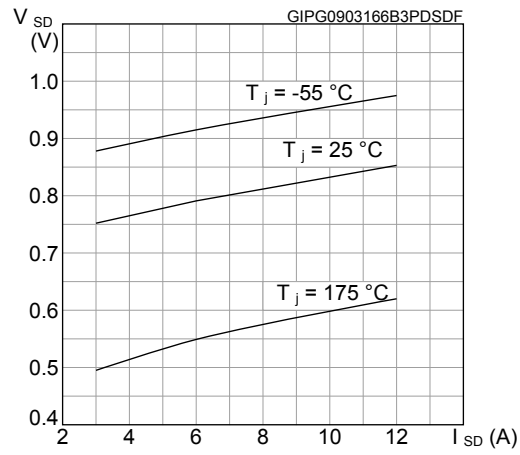
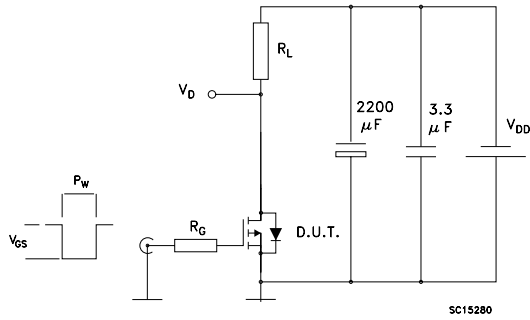
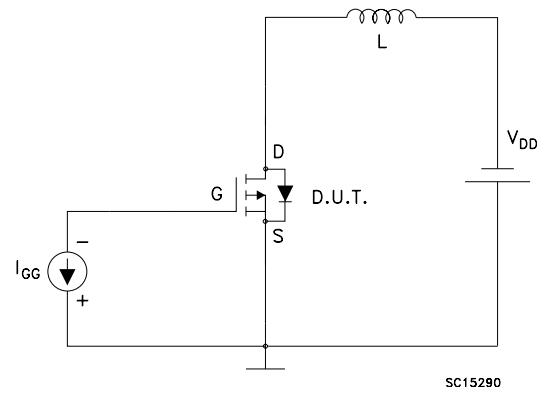
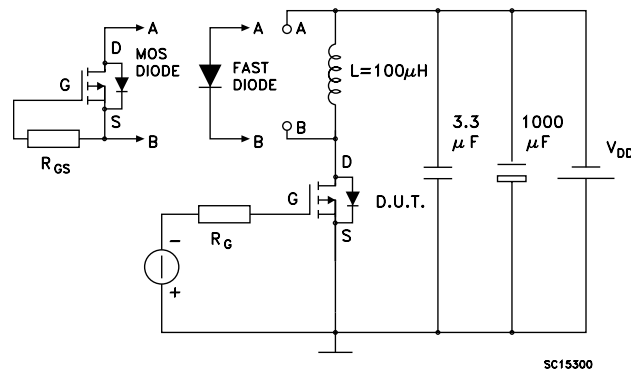


Figure 11. Source-drain diode forward characteristics



3 Test circuits

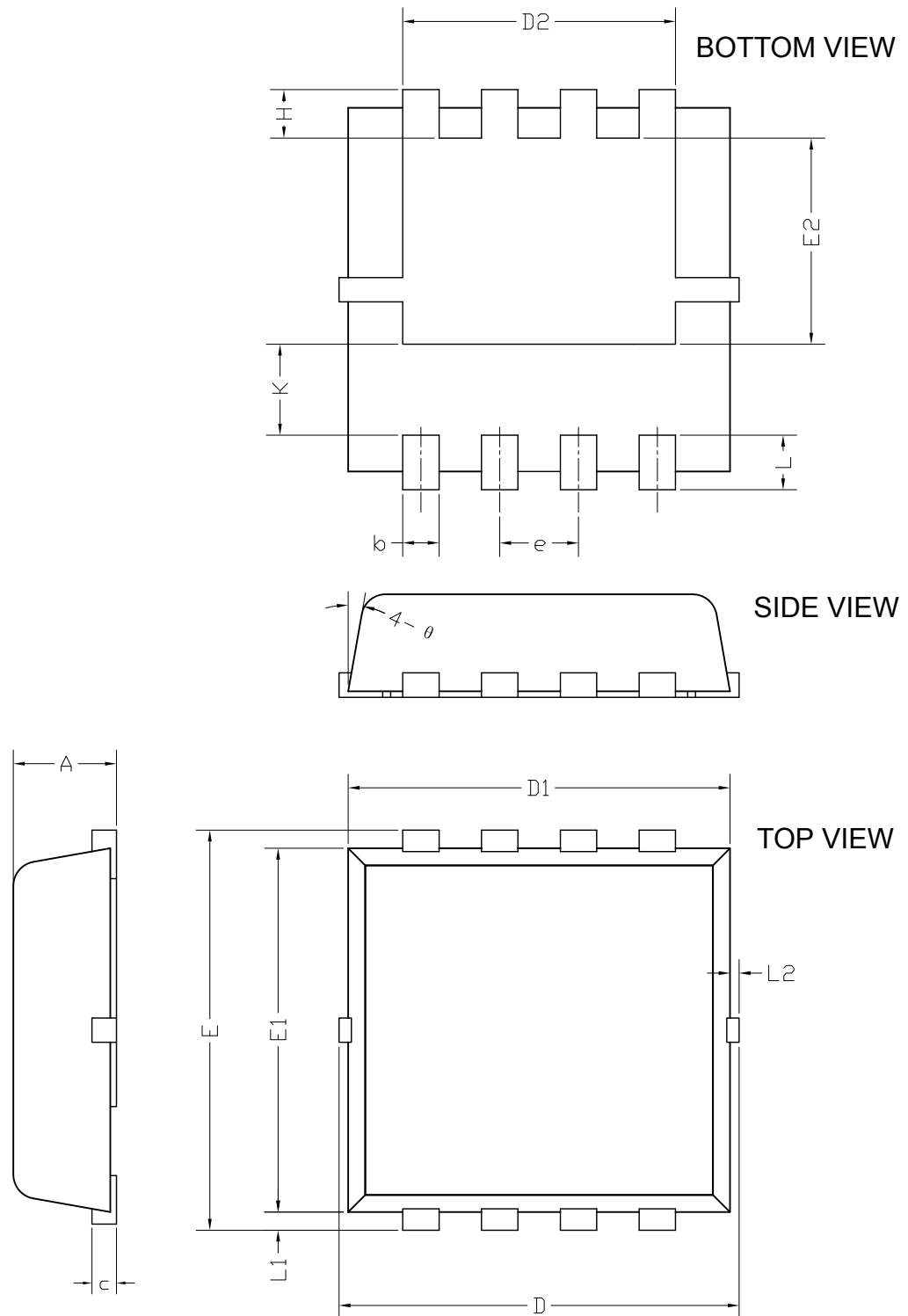
Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

Figure 14. Test circuit for inductive load switching and diode recovery times


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 3.3x3.3 package information

Figure 15. PowerFLAT™ 3.3x3.3 package outline

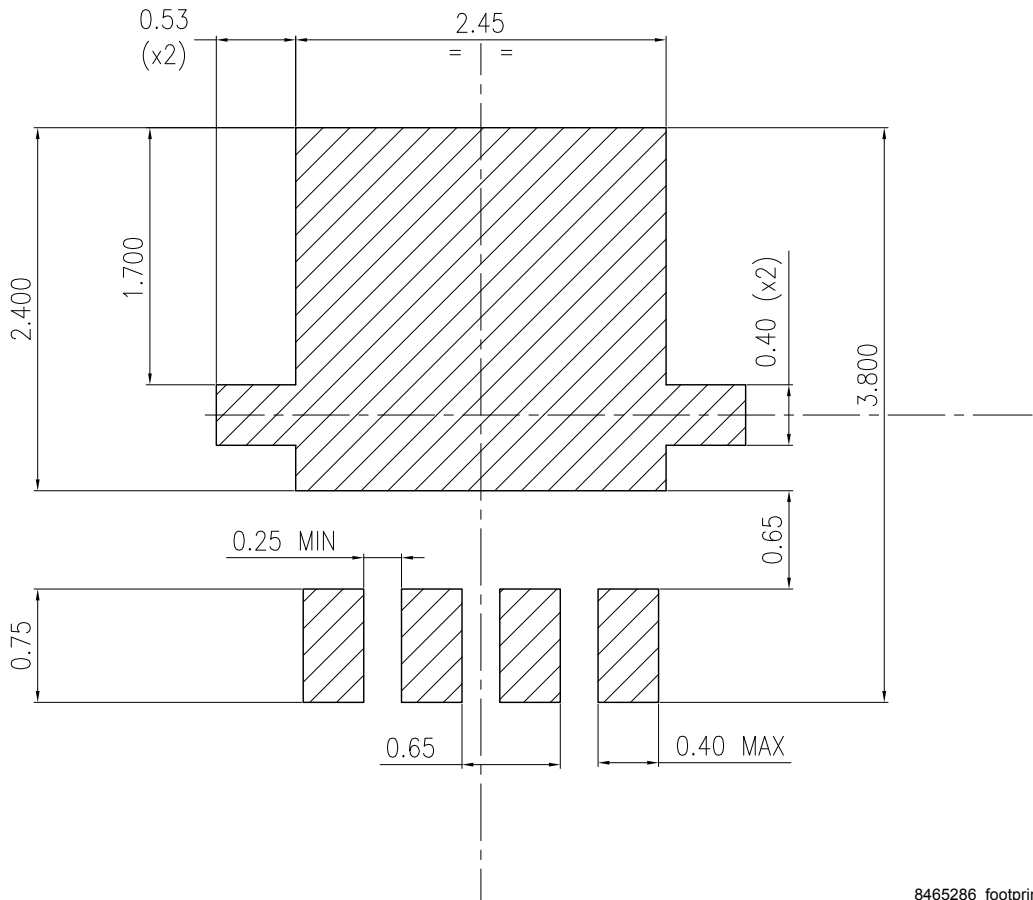


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Table 7. PowerFLAT™ 3.3x3.3 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	0.30	0.45	0.60
L1	0.05	0.15	0.25
L2			0.15
θ	8°	10°	12°

Figure 16. PowerFLAT™ 3.3x3.3 recommended footprint (dimensions are in mm)



8465286_footprint

Revision history

Table 8. Document revision history

Date	Revision	Changes
23-Jan-2014	1	First release.
07-Mar-2016	2	Modified: title and $R_{DS(on)}$ max value Modified: <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "On /off states"</i> , <i>Table 5: "Dynamic"</i> , <i>Table 6: "Switching times"</i> and <i>Table 7: "Source drain diode"</i> Minor text changes.
20-Feb-2018	3	Updated Figure 1. Safe operating area and Figure 2. Thermal impedance . Removed maturity status indication from cover page. The document status is production data.

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